



# NX7002BKMB

60 V, N-channel Trench MOSFET

3 December 2014

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2kV HBM

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	60	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	350	mA
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 200\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	2.2	2.8	$\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $1\text{ cm}^2$ .

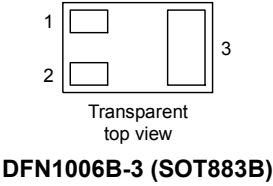
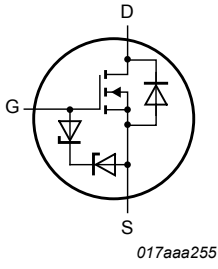


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>Transparent top view <b>DFN1006B-3 (SOT883B)</b></p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

## 6. Ordering information

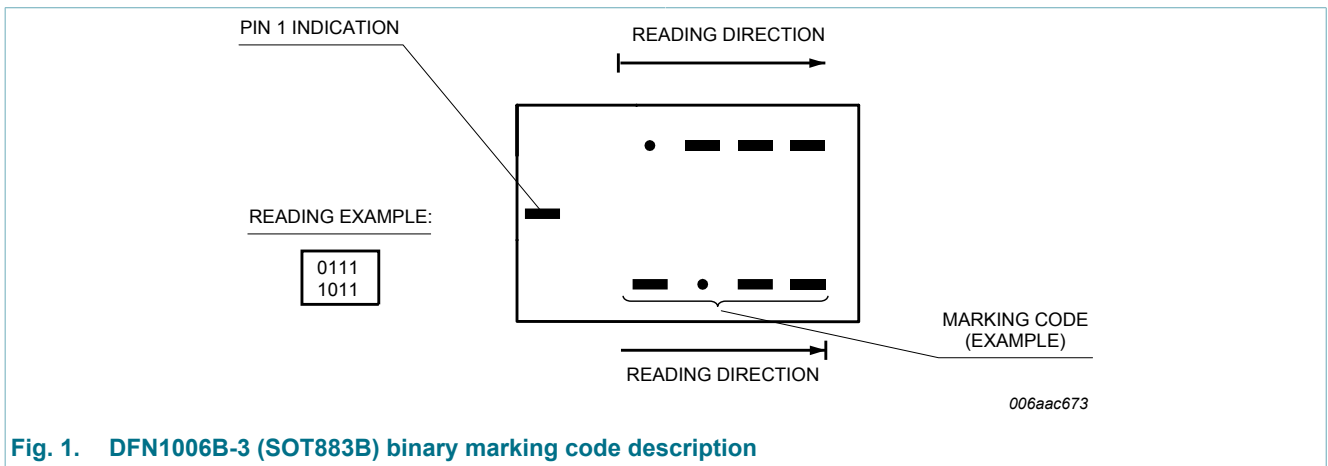
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX7002BKMB	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

## 7. Marking

Table 4. Marking codes

Type number	Marking code
NX7002BKMB	0101 0111



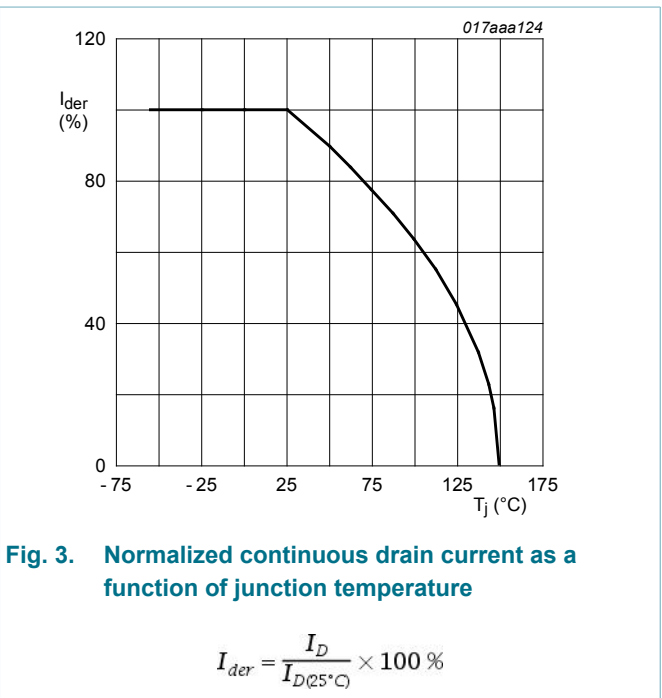
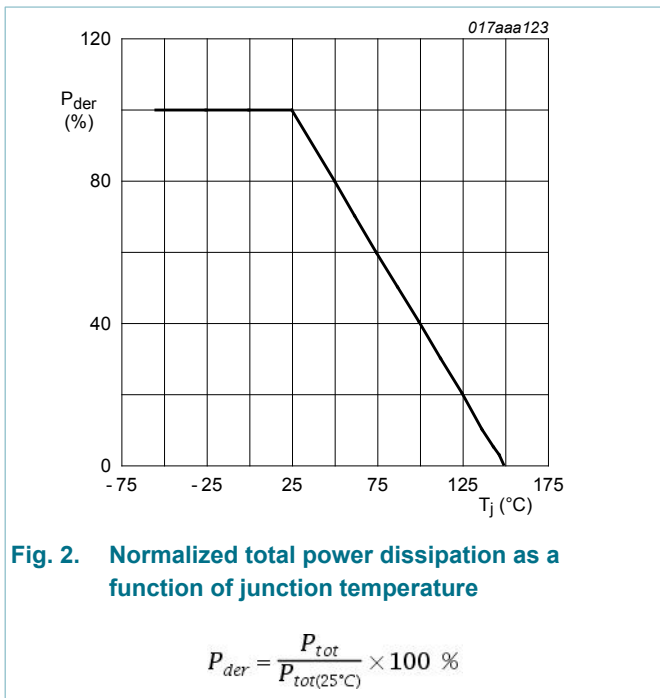
## 8. Limiting values

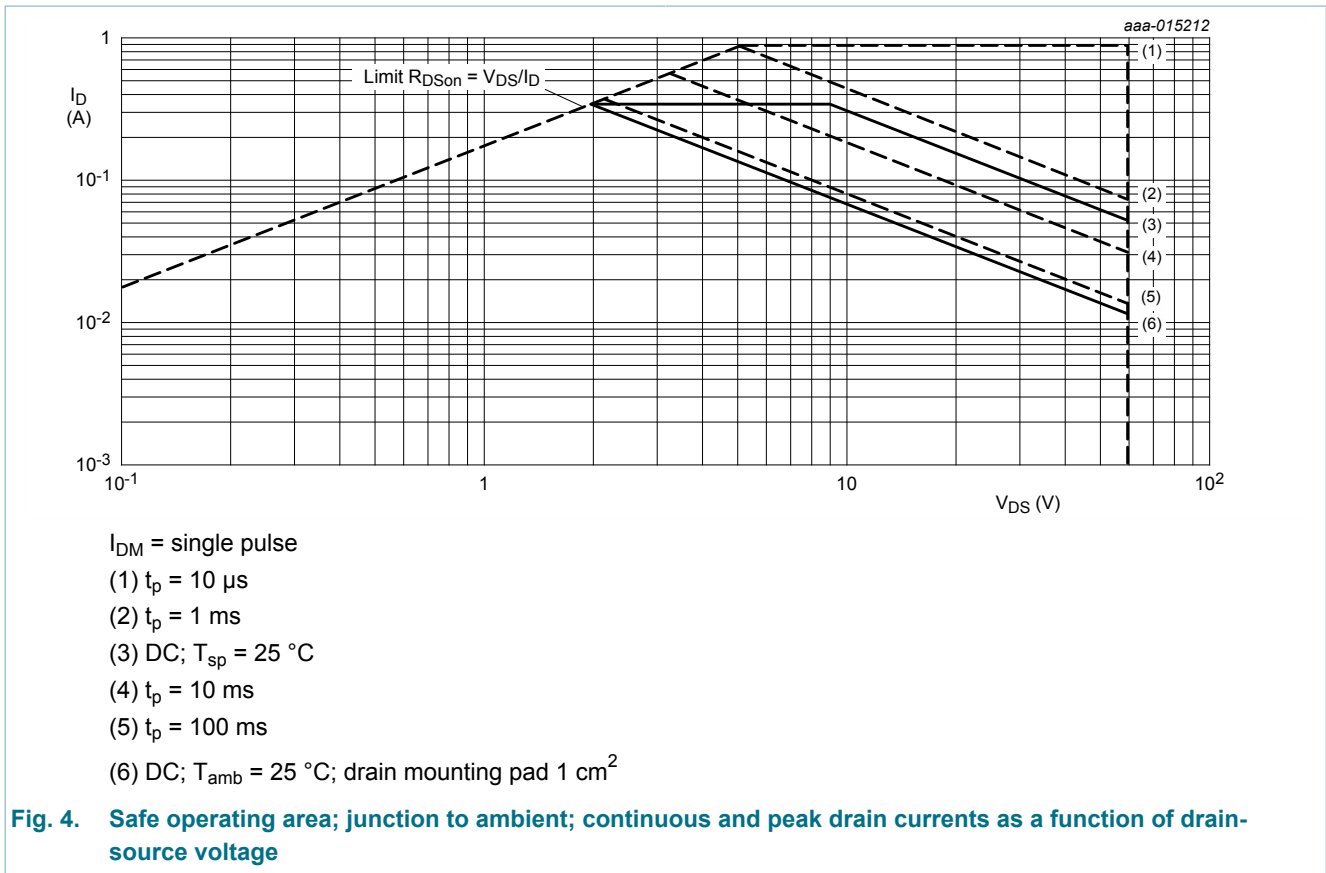
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	350	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	200	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	0.9	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	680	mW
		T <sub>sp</sub> = 25 °C		-	3100	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.





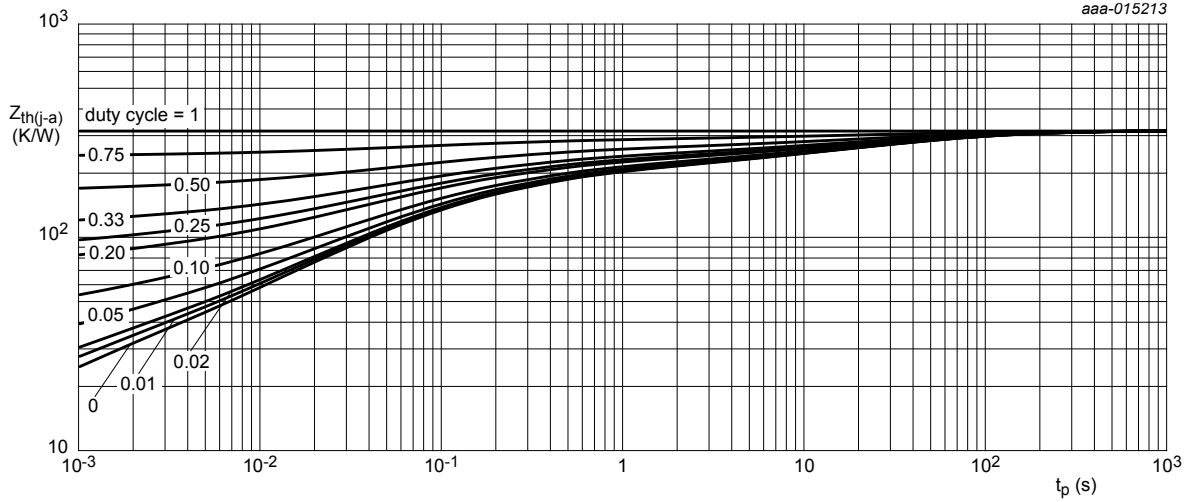
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	314	360	K/W
			[2]	-	159	180	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	35	40	K/W

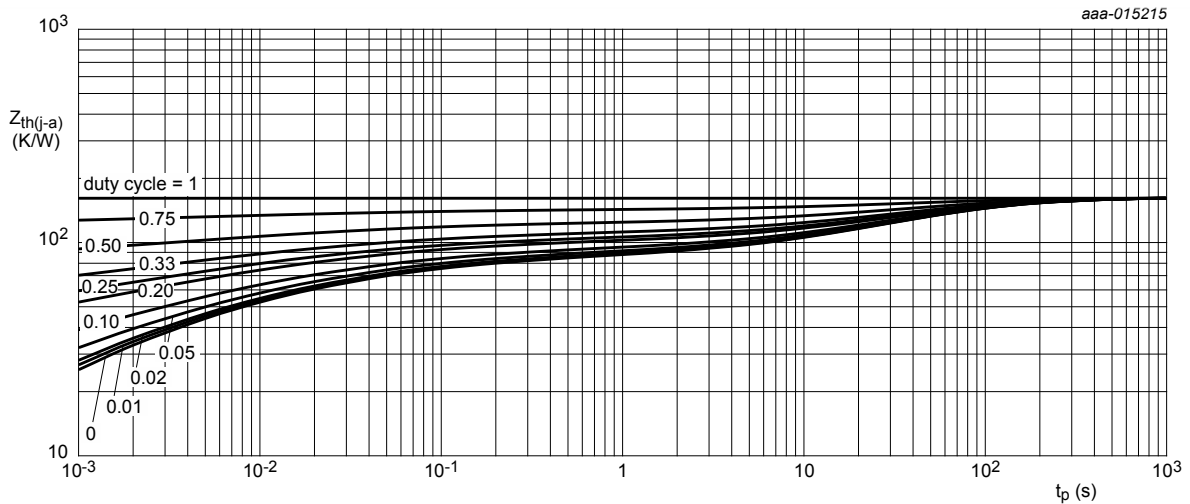
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $1 \text{ cm}^2$ .



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



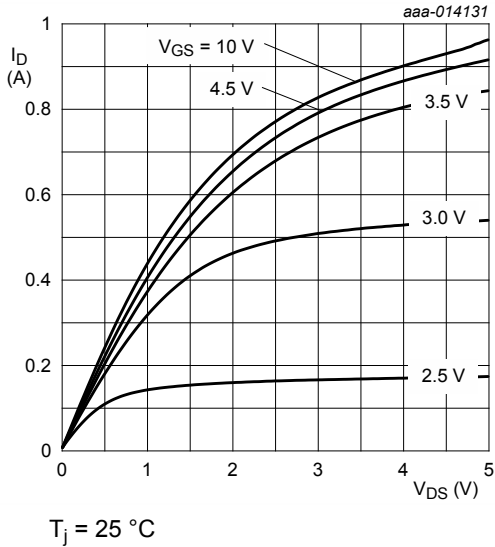
FR4 PCB, mounting pad for drain  $1\text{ cm}^2$

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

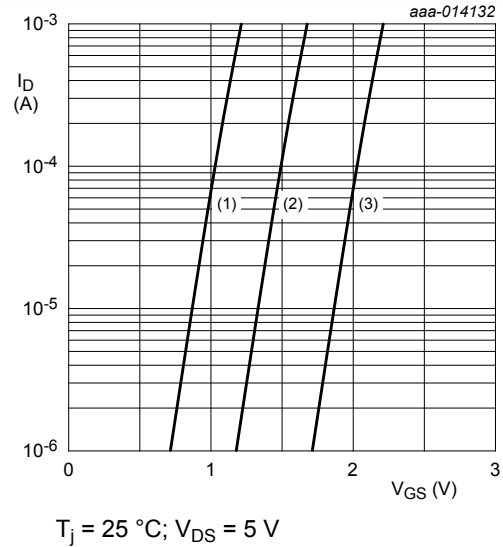
## 10. Characteristics

Table 7. Characteristics

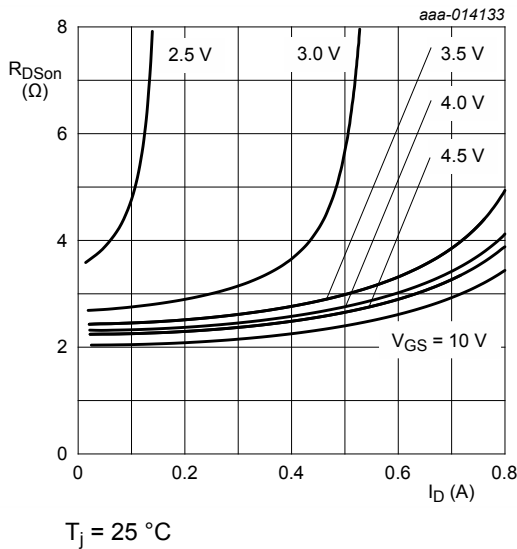
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.1	1.6	2.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	$\mu A$
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
		$V_{GS} = 5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	0.3	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2.2	2.8	$\Omega$
		$V_{GS} = 10 V; I_D = 100 \text{ mA}; T_j = 150 \text{ }^\circ C$	-	4.5	5.7	$\Omega$
		$V_{GS} = 5 V; I_D = 200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2.5	3.2	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V; I_D = 200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	600	-	mS
$R_G$	internal gate resistance (AC)	$f = 2.5 \text{ MHz}$	-	2.5	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 V; I_D = 200 \text{ mA}; V_{GS} = 10 V; T_j = 25 \text{ }^\circ C$	-	1	-	nC
$Q_{GS}$	gate-source charge		-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.18	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 10 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	23.6	-	pF
$C_{oss}$	output capacitance		-	4.6	-	pF
$C_{rss}$	reverse transfer capacitance		-	3	-	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 50 V; I_D = 200 \text{ mA}; V_{GS} = 10 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	4.7	-
$t_r$	rise time	-		4.3	-	ns
$t_{d(off)}$	turn-off delay time	-		6.9	-	ns
$t_f$	fall time	-		2.9	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 200 \text{ mA}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.87	1.2	V



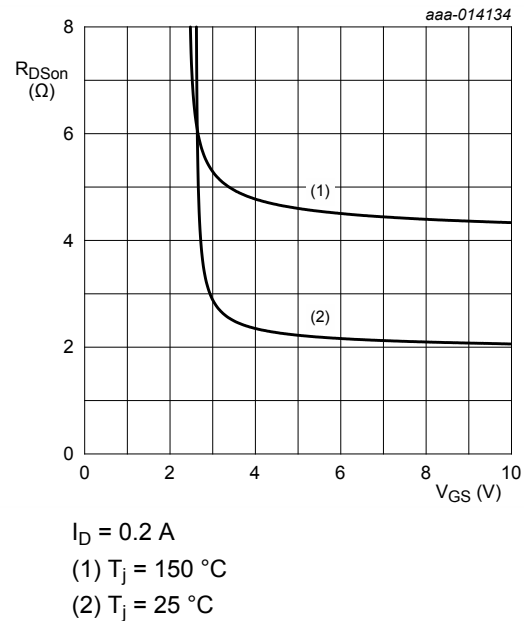
**Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values**



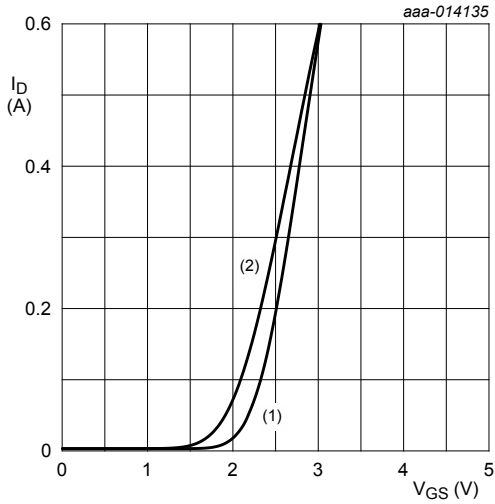
**Fig. 8. Sub-threshold drain current as a function of gate-source voltage**  
 (1) minimum values  
 (2) typical values  
 (3) maximum values



**Fig. 9. Drain-source on-state resistance as a function of drain current; typical values**

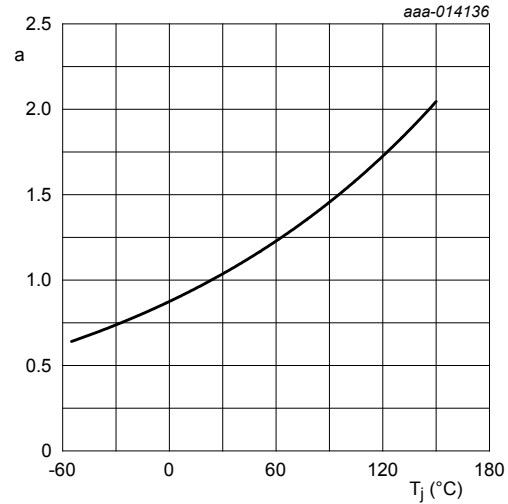


**Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values**



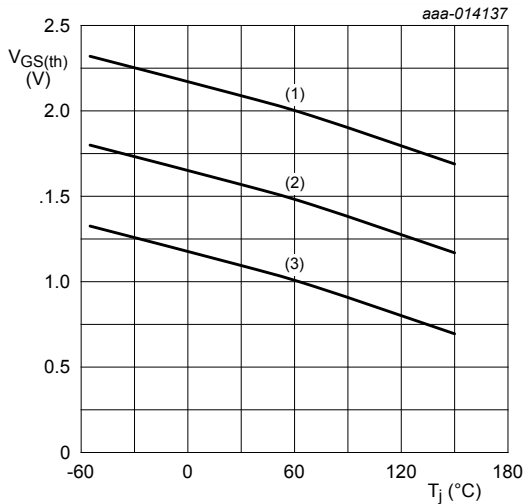
$V_{DS} > I_D \times R_{DSon}$   
 (1)  $T_j = 25\text{ }^\circ\text{C}$   
 (2)  $T_j = 150\text{ }^\circ\text{C}$

**Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



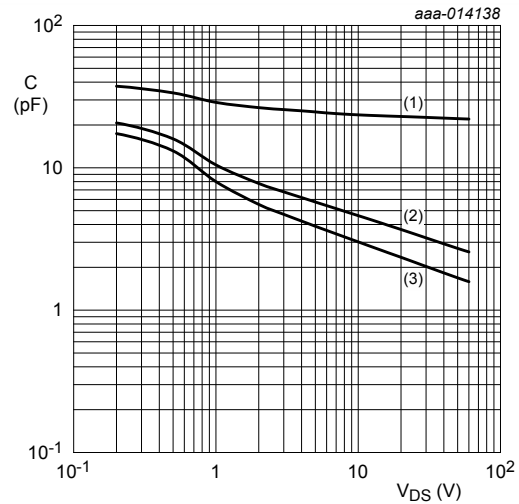
**Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$



$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

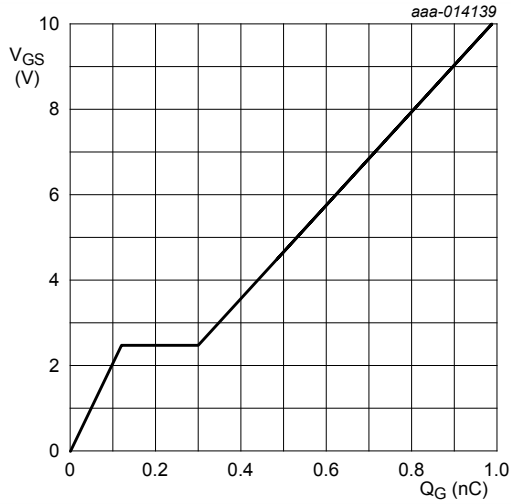
**Fig. 13. Gate-source threshold voltage as a function of junction temperature**



$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



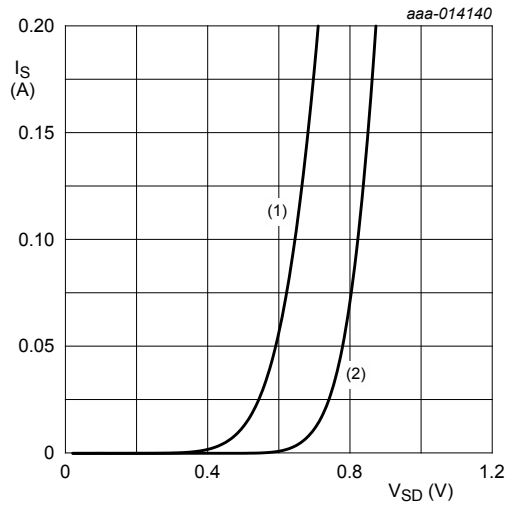


$I_D = 0.2 \text{ A}$ ;  $V_{DS} = 30 \text{ V}$ ;  $T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 15. Gate-source voltage as a function of gate charge; typical values**



**Fig. 16. MOSFET transistor: Gate charge waveform definitions**



$V_{GS} = 0 \text{ V}$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$   
 (2)  $T_j = 25 \text{ }^\circ\text{C}$

**Fig. 17. Source current as a function of source-drain voltage; typical values**

11. Test information

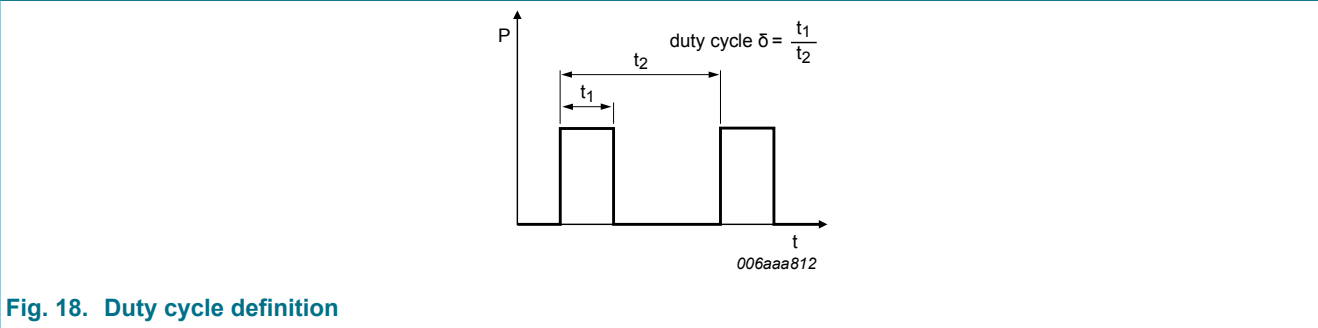


Fig. 18. Duty cycle definition

## 12. Package outline

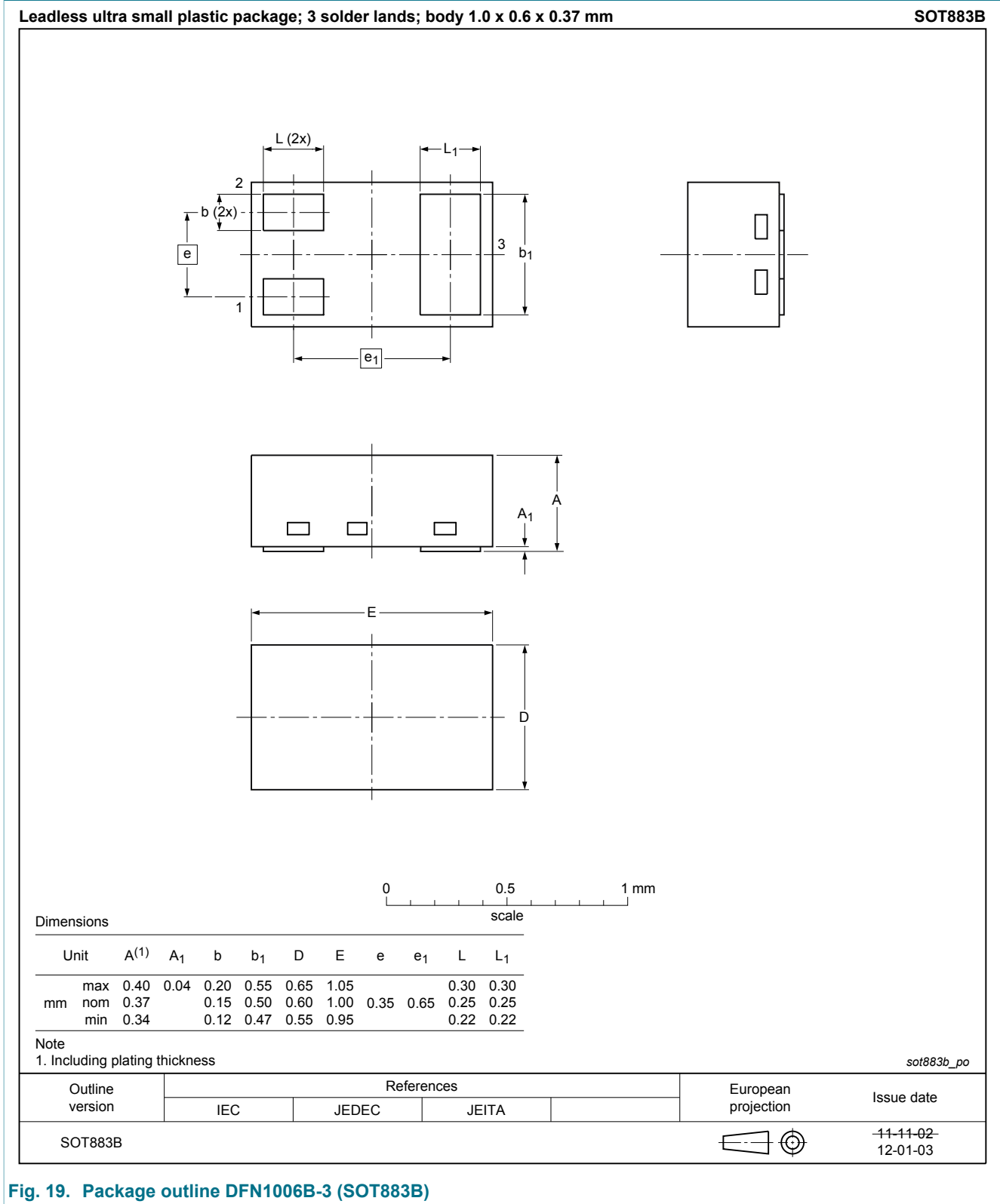


Fig. 19. Package outline DFN1006B-3 (SOT883B)

### 13. Soldering

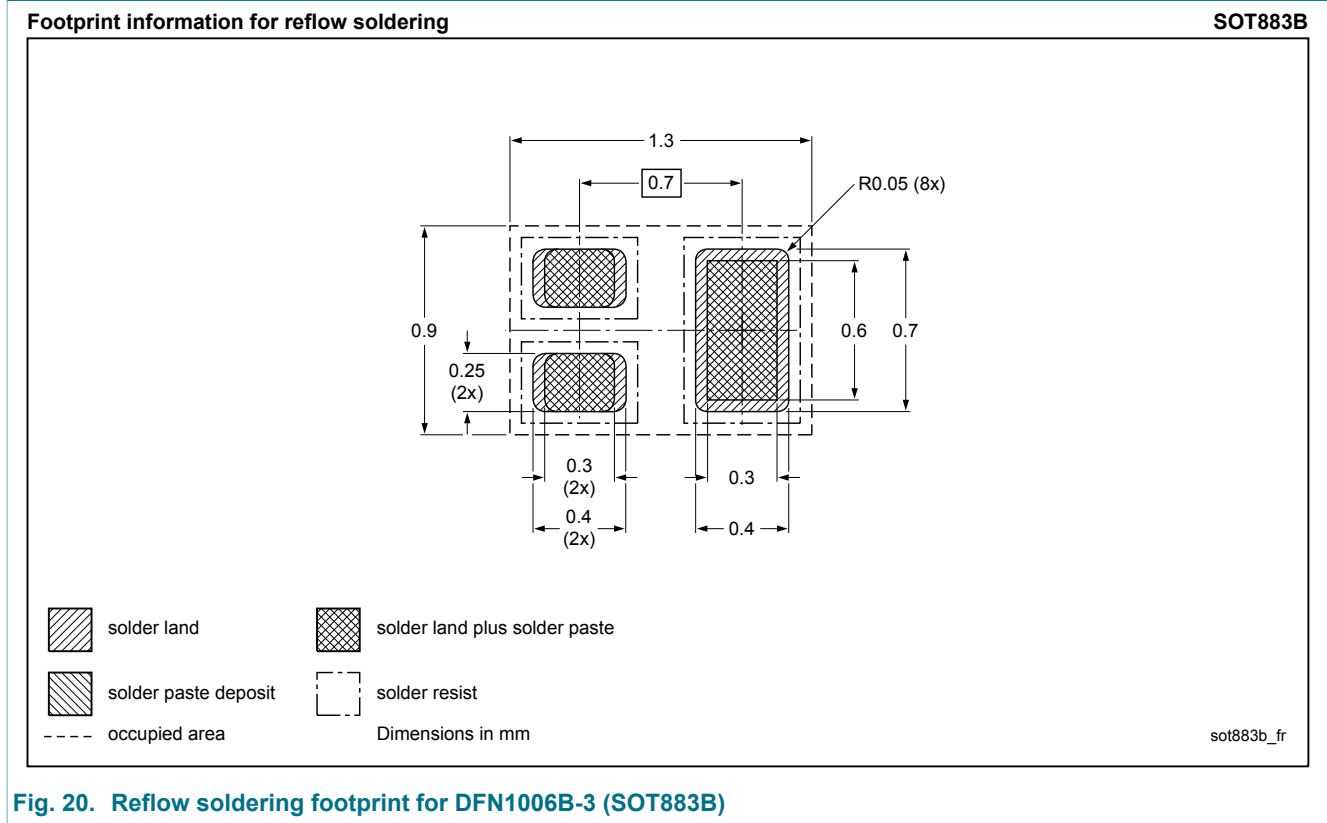


Fig. 20. Reflow soldering footprint for DFN1006B-3 (SOT883B)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002BKMB v.2	20141203	Product data sheet	-	NX7002BKMB v.1
Modification:	• Figure 3 updated			
NX7002BKMB v.1	20141001	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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